

2SC5397

For High Frequency Amplify, Medium Frequency Amplify
Silicon NPN Epitaxial Type Micro(Frame type)

DESCRIPTION

2SC5397 is a silicon NPN epitaxial type transistor.

FEATURE

- High gain 10.7MHz MAG=45dB typ
- Low noise 10.7MHz NF=3.0dB typ
- Low yre 10.7MHz yre=-j0.11mS typ
- Small package

APPLICATION

High frequency amplify, oscillating, frequency exchange, medium frequency amplify for small communication machine, FM/AM radio.

MAXIMUM RATINGS (Ta=25°C)

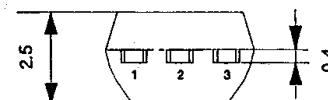
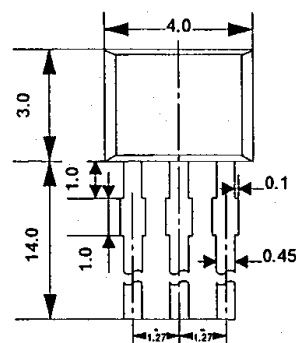
SYMBOL	PARAMETER	RATINGS	UNIT
V _{CB0}	Collector to Base voltage	30	V
V _{EB0}	Emitter to Base voltage	4	V
V _{CEO}	Collector to Emitter voltage	25	V
I _C	Collector current	30	mA
P _C	Collector dissipation (Ta=25°C)	450	mW
T _J	Junction temperature	+125	°C
T _{stg}	Storage temperature	-55to+125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
I _{CB0}	Collector cut off current	V _{CB} =30V, I _E =0			1	μA
I _{EB0}	Emitter cut off current	V _{EB} =4V, I _C =0			1	μA
h _{FE} *	DC forward current gain	V _{CE} =6V, I _C =1mA	35		300	—
f _T	Gain band width product	V _{CE} =6V, I _E =-1mA	150	200		MHz
C _{ob}	Collector output capacitance	V _{CB} =6V, I _E =0, f=1MHz		2.0	2.7	pF
C _{crb'b}	Base time constant	V _{CB} =6V, I _E =-1mA, f=31.8MHz		20	60	pS
NF	Noise figure	V _{CE} =6V, I _E =-1mA, f=10.7MHz, R _G =500Ω		3.0		dB

OUTLINE DRAWING

UNIT:mm



TERMINAL CONNECTOR

- ① : EMITTER
② : COLLECTOR
③ : BASE
- EIAJ : —
JEDEC : —

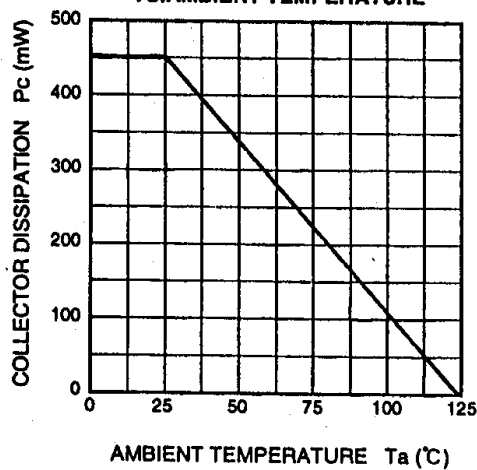
ITEM	B	C	D	E
h _{FE}	35~70	55~110	90~180	150~300

2SC5397

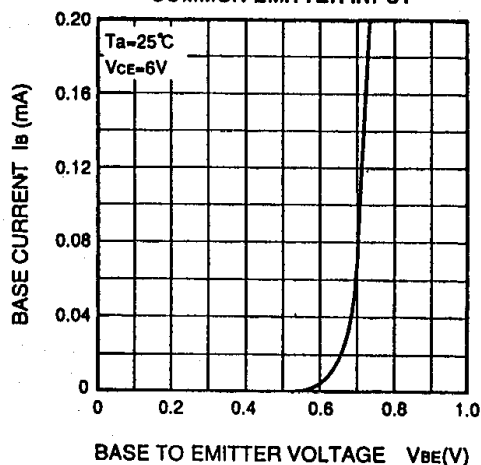
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TYPICAL CHARACTERISTICS

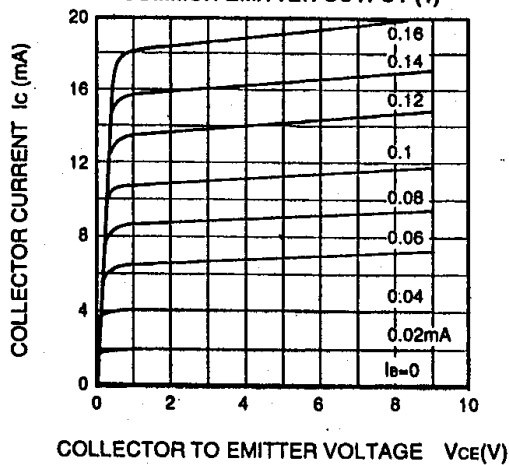
COLLECTOR DISSIPATION
VS. AMBIENT TEMPERATURE



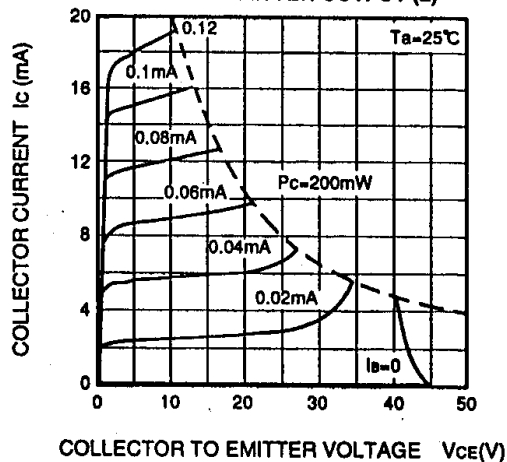
COMMON EMITTER INPUT



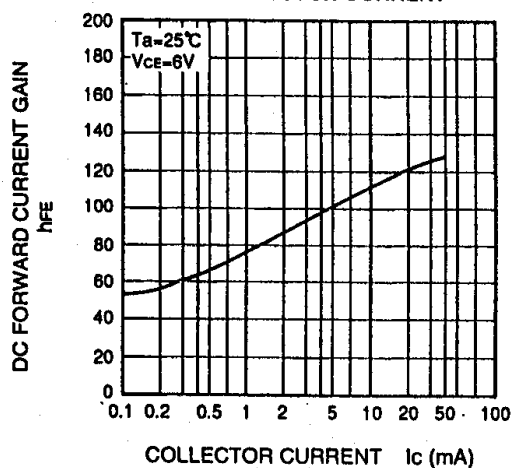
COMMON EMITTER OUTPUT (1)



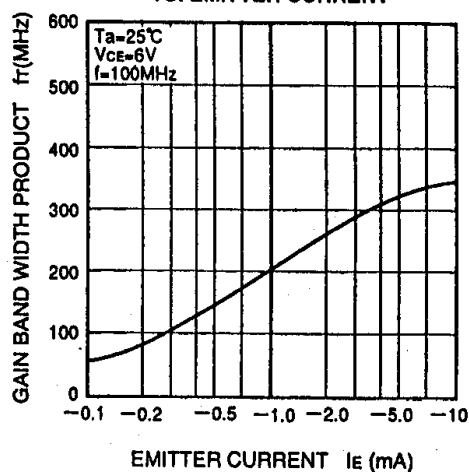
COMMON EMITTER OUTPUT (2)



DC FORWARD CURRENT GAIN
VS. COLLECTOR CURRENT



GAIN BAND WIDTH PRODUCT
VS. EMITTER CURRENT

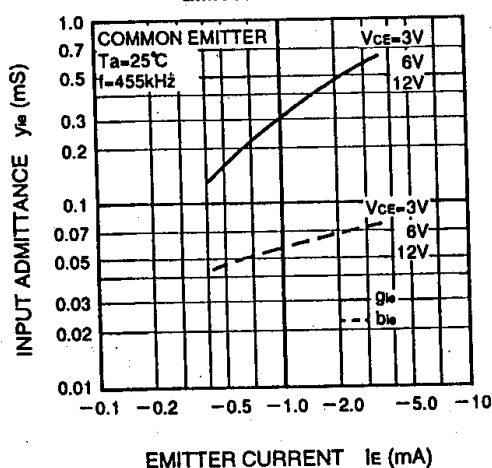


COMMON EMITTER, y PARAMETER (TYPICAL VALUE)

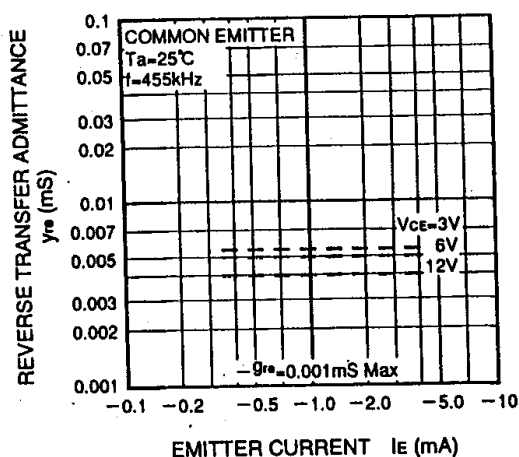
Test conditions		f=455kHz VCE=6V IE=-1mA	f=1MHz VCE=6V IE=-1mA	f=10.7MHz VCE=6V IE=-1mA	f=100MHz VCE=6V IE=-1mA
y Parameter	gie	0.30	0.30	0.38	4.4
	bie	0.06	0.12	1.40	11.0
yre	-gre	0.001Max	0.001Max	0.005Max	0.05Max
	-bre	0.005	0.010	0.11	1.0
yle	gie	50	46	37	25
	-bie	1.0Max	1.0Max	2.8	16
yoe	goe	0.010	0.012	0.03	0.32
	boe	0.011	0.022	0.18	1.3

COMMON EMITTER, 455kHz y PARAMETER

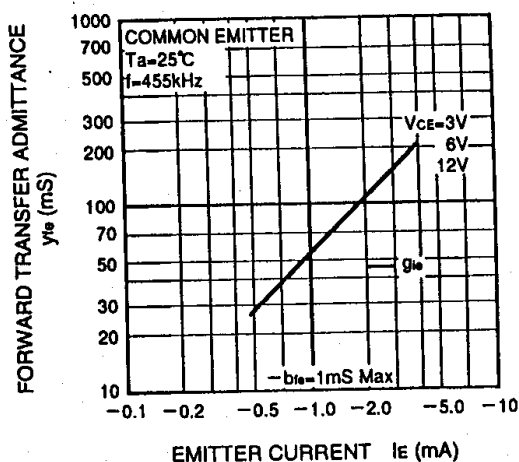
INPUT ADMITTANCE VS.
EMITTER CURRENT



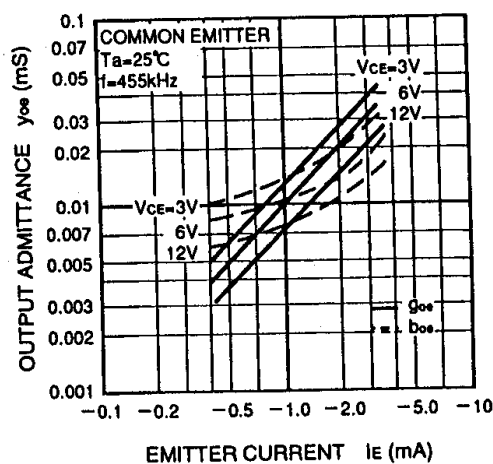
REVERSE TRANSFER ADMITTANCE
VS. EMITTER CURRENT



FORWARD TRANSFER ADMITTANCE
VS. EMITTER CURRENT



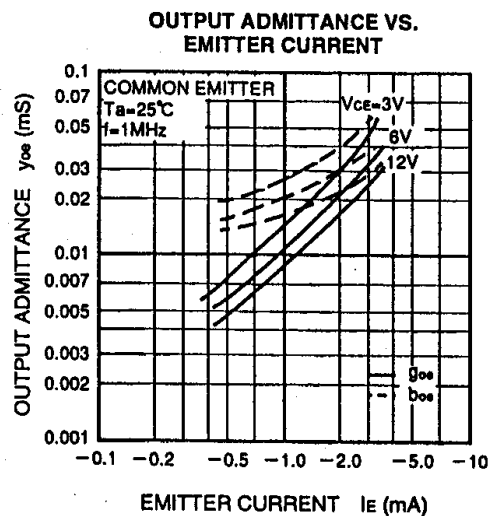
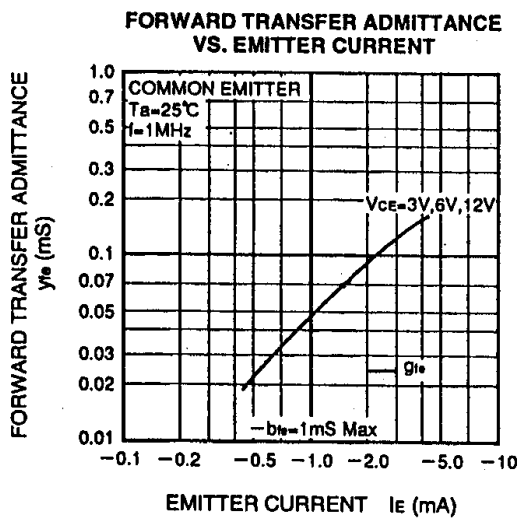
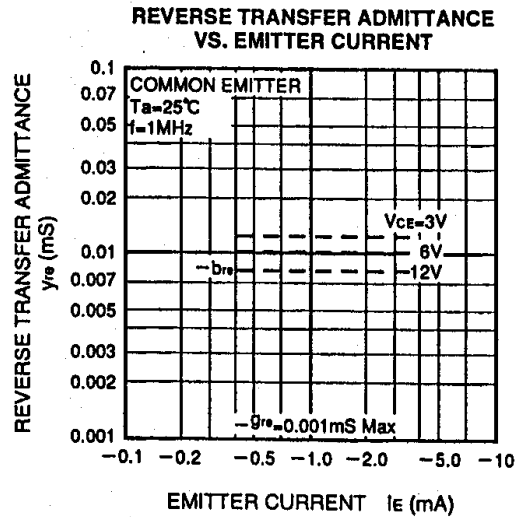
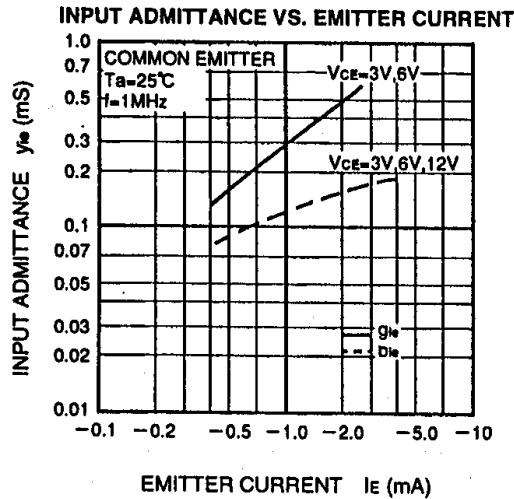
OUTPUT ADMITTANCE VS.
EMITTER CURRENT



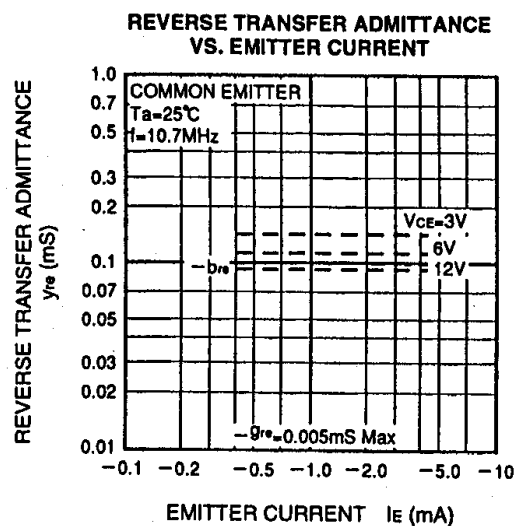
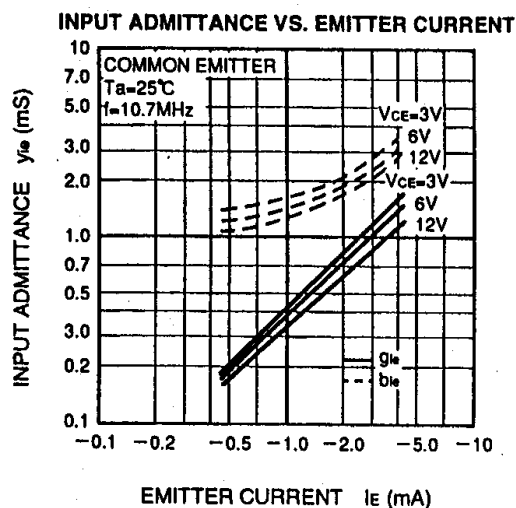
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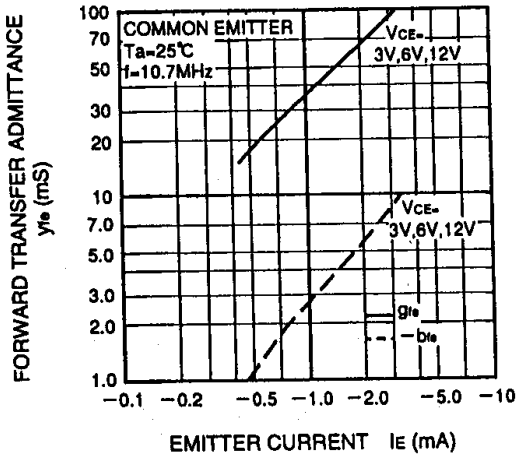
COMMON EMITTER, 1MHz y PARAMETER



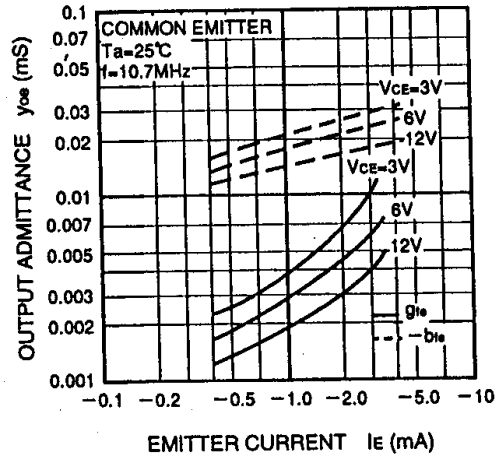
COMMON EMITTER, 10.7MHz y PARAMETER



FORWARD TRANSFER ADMITTANCE
VS. EMITTER CURRENT

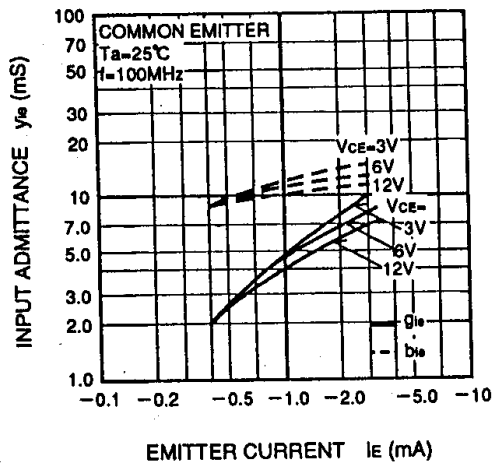


OUTPUT ADMITTANCE VS. EMITTER CURRENT

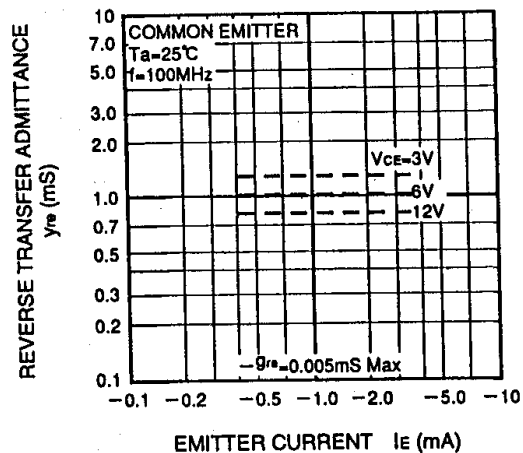


COMMON EMITTER, 100MHz y PARAMETER

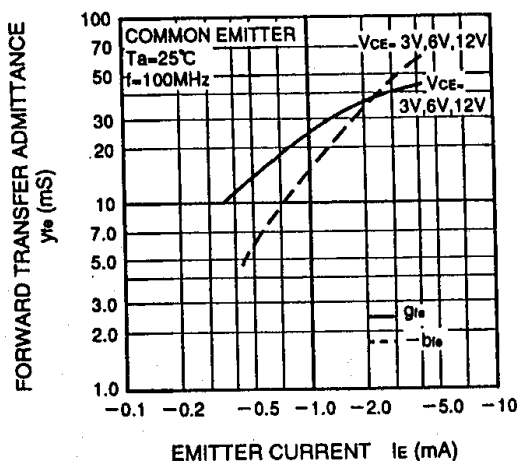
INPUT ADMITTANCE VS. EMITTER CURRENT



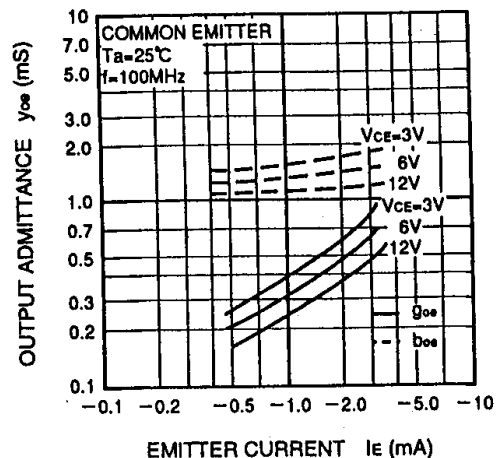
REVERSE TRANSFER ADMITTANCE
VS. EMITTER CURRENT



FORWARD TRANSFER ADMITTANCE
VS. EMITTER CURRENT



OUTPUT ADMITTANCE VS.
EMITTER CURRENT





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